

Gaudenzio MENEGHESSO

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BOOK CHAPTER

- B1 E. Zanoni, **G. Meneghesso**, "Impact Ionization in Compound Semiconductor Devices", **Book Chapter in Handbook of Advanced Electronic and Photonic Materials and Devices**, edited by. H. S. Nalwa, Vol. 2 – Semiconductor Devices, Chapter 2, pp. 67-131, 2001.
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R206 ESREF Dal Lago

R207 Efficiency droop in InGaN/GaN blue light-emitting diodes: physical mechanisms and remedies,
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